

The PowerAmerica Institute at NC State seeks to save energy and create U.S. manufacturing jobs by accelerating the development and large-scale adoption of SiC and GaN wide bandgap semiconductor technology in power electronic systems. We work across the supply chain, bringing together industry, academia and national lab partners to form a wide bandgap manufacturing ecosystem.

## PowerAmerica Members Presenting at APEC 2019

	Time	Room	Title and Presenter
		KOOIII	
.8 <b>SUN.</b> 3/17	9:30 a.m1 p.m.		PE SEMINAR: Design & Integration of WBG Solid State Circuit Protection Douglas Hopkins, NC State University
	9:30 a.m1 p.m.		PE SEMINAR: Design Issues for High Power and High Performance SiC Converters  Jiangbio He, Juan Sabate, Michael Schutten, Yash Veer Singh, Zheyu Zhang, GE Global Research Center
	9:30 a.m.–1 p.m.		PE SEMINAR: WBG Device Characterization for Converter Design: Challenges and Solutions GE Global Research; University of Tennessee at Knoxville
	2:30-6 p.m.		PE SEMINAR: High Power and Medium Voltage Applications of Wide Bandgap Power Devices Jin Wang and Mark Scott, The Ohio State University
	2:30-6 p.m.		PE SEMINAR: Ten Most Commonly Asked Questions on Migrating from Si to SiC MOSFET-based Converter Designs David Levett, Infineon
	8:30 a.m12 p.m.		PE SEMINAR: Systematic Approach to Control of Electric Drives and 3 Phase Converters Tony O'Gorman and Vladimir Blasko, UTRC
MON. 3/18	8:30 a.m.–12 p.m.		PE SEMINAR: Simulation and Analysis Applied to the Design of Buck Topologies Christopher Basso, ON Semiconductor
Σ	8:30 a.m12 p.m.		PE SEMINAR: What Makes SiC Better and How Do I Change My System to Benefit Xuning Zhang, Monolith Semiconductor
<b>TUE.</b> 3/19	8:30 a.m.–12 p.m.	212AB	TECHNICAL SESSION: Power Converter Modeling and Simulation Analytical Analysis of AC and DC Side Harmonics of Three-Level Active Neutral Point Clamped Inverter with Space Vector Modulation Fred Wang, Leon M. Tolbert and Daniel J. Costinett, University of Tennessee-Knoxville
	8:30 a.m12 p.m.	213C	TECHNICAL SESSION: Photovoltaic Power Conversion Systems Power Pulsation Decoupling in a Series-Stacked PV-Battery Inverter Namwon Kim and Babak Parkhideh, University of North Carolina-Charlotte
	8:30 a.m12 p.m.	213D	TECHNICAL SESSION: Control of DC-DC Converters Simplified Optimal Trajectory Control for 1 MHz LLC Converter with Wide Input Voltage Range Qiang Li and Fred C. Lee, Virginia Tech Dynamic Interleaving of Multi-Phase Synchronous DC-DC Converters with ZVS Wensong Yu and Iqbal Husain, NC State University
	8:30 a.m12 p.m.	303AB	TECHNICAL SESSION: Drives & Inverters: Topologies & Control Coupled Inductor Design for Interleaved Three-Level Active Neutral Point Clamped Inverters Considering EMI Noise Reduction Fred Wang, Leon M. Tolbert, Daniel J. Costinett, University of Tennessee-Knoxville
	8:30 a.m12 p.m.	304CD	TECHNICAL SESSION: WBG Applications  Design Considerations of High-Voltage-Insulated Gate Drive Power Supply for 10 kV SiC MOSFET in Medium-Voltage Application Fred Wang and Leon M. Tolbert, University of Tennessee-Knoxville  A Reliable Ultra-Fast Three Step Short Circuit Protection Method for E-Mode GaN HEMTs  Jin Wang, The Ohio State University and Sandeep Bala, ABB  Benchmarking and Qualification of Gate Drivers for Medium Voltage (MV) Operation Using  10 kV SiC MOSFETs Subhashish Bhattacharya, NC State University
	8:30-11:55 a.m.	210D	INDUSTRY SESSION: Getting Up to Speed on Switching: Wide Bandgap and Other High Performance Components High Performance SiC MOSFETs and Diodes Fabricated in High-Volume 6-Inch CMOS Fab Sujit Banerjee, Monolith and Christophe Warin, Microsemi Avalanche and Short-circuit Robustness of High Voltage SiC DMOSFETs Ranbir Singh, GeneSiC CoolSiC Power MOSFETs: New Additions to the Portfolio Peter Friedrichs, Infineon How GaN Helps Power Supplies Achieve Extraordinary Levels of Efficiency Eric Persson, Infineon
	8:30-11:55 a.m.	213B	INDUSTRY SESSION: Market Research What Can The Power Electronics Industry Expect from SiC & GaN? Ana Villamor, ON Semiconductor
	5-6:30 p.m.	Ballroom D	RAP SESSION: When Will WBG Have Significant Volume? Is the System Benefit Worth the Cost? Is WBG Reliable? Sandeep Bala, ABB; Tim McDonald, Infineon; Chris Dries, United SiC

	Time	Room	Title and Presenter
<b>WED.</b> 3/20	8:30-10:10 a.m.	212AB	TECHNICAL SESSION: Power Device and Modeling Chair: Sandeep Bala, ABB and Rolando Burgos, Virginia Tech New Dynamic Power MOSFET Model to Determine Maximum Device Operating Frequency Jayant Baliga and Douglas Hopkins, NC State University
	8:30-10:10 a.m.	213C	TECHNICAL SESSION: Microgrid Applications Operation of a Flexible Dynamic Boundary Microgrid with Multiple Islands Fred Wang and Leon Tolbert, University of Tennessee-Knoxville
	8:30-10:10 a.m.	213D	TECHNICAL SESSION: Rectifiers for EV Charging A 12.47 kV Medium Voltage Input 350 kW EV Fast Charger Using 10 kV SiC MOSFETs Srdjan Lukic, N.C. State University
	8:30-10:10 a.m.	304AB	TECHNICAL SESSION: Optimization of Wireless Power Transfer Systems Soft Switching Realization of LCCL-LC Resonant Converter for Wireless Power Transfer Application Qiang Li and Fred C. Lee, Virginia Tech
	8:30-10:10 a.m.	210BC	INDUSTRY SESSION: GaN in the Data Center eGaN Based High-Density Unregulated 48 V to x V LLC Converters with ≥ 98% Efficiency for Future Data Centers Fred C. Lee and Qiang Li, Virginia Tech
	8:30-10:10 a.m.	210D	INDUSTRY SESSION: Modules Chair: David Levett, Infineon A Modular and Scalable High Performance Power Module for Silicon Carbide Devices Ty McNutt, Wolfspeed-Fayetteville A Medium Voltage (10 kV), Low Inductance, SiC Power Module for Next-Generation Electric Power Distribution Applications Ty McNutt, Wolfspeed-Fayetteville
	2-5:30 p.m.	211AB	TECHNICAL SESSION: Single-Phase AC-DC Converters Chair: Qiang Li, Virginia Tech Inductor Design and ZVS Control for a GaN-Based High Efficiency CRM Totem-Pole PFC Converter Daniel J. Costinett and Leon M. Tolbert, University of Tennessee-Knoxville
	2-5:30 p.m.	213C	TECHNICAL SESSION: Wireless Power Transfer Applications Design and Evaluation of a Multilevel Switched Capacitor Rectifier for Wireless Fast Charging Daniel J. Costinett, University of Tennessee-Knoxville
	2-5:30 p.m.	303AB	TECHNICAL SESSION: Driving WBG Devices Chair: Alireza Dayerizadeh, NC State In Depth Analysis of Driving Loss and Driving Power Supply Structure for SiC MOSFETs Sujit Banerjee, Monolith Semiconductor Current Source Gate Drive to Reduce Switching Loss for SiC MOSFETs Leon M. Tolbert, Fred Wang, and Daniel J. Costinett, University of Tennessee-Knoxville
	2-5:30 p.m.	303CD	TECHNICAL SESSION: Drivers and Inverters: Parameter Identification, Measurement and Diagnostics Phase Current Reconstruction Based on Rogowski Coils Integrated on Gate Driver of SiC MOSFET Half-Bridge Module for Continuous and Discontinuous PWM Inverter Applications Rolando Burgos, Virginia Tech; Marko Jaksic, Mehrdad Teimor and Brian Peaslee, General Motors
	2-5:30 p.m.	304CD	TECHNICAL SESSION: Transportation/Storage/Grid Stability Analysis of a Medium Voltage Cascaded Converter System with Reduced DC-Link Capacitance Subhashish Bhattacharya, N.C. State
	2-5:25 p.m.	210A	INDUSTRY SESSION: Making Power Sources Small with 3-D Packaging Solutions Efficient Grid-to-Battery Power Electronics for EVs Ty McNutt, Wolfspeed-Fayetteville; Dave Grider and Edward Van Brundt, Wolfspeed
	2-5:25 p.m.	210BC	INDUSTRY SESSION: Enablers for Transportation Electrification Silicon Carbide Inverter Development, Inverter Testing and Findings from Heavy-Duty Vehicles Brij Singh, John Deere Holistic Thermal Management Kevin Bennion, NREL
	2-5:25 p.m.	210D	INDUSTRY SESSION: Current Reliability and Product Qualification Topics for SiC and GaN Wide Bandgap Devices  Meeting Industry Requirements for GaN Device Reliability Tim McDonald, Infineon Performance, Reliability and Yield Considerations in State-of-the-Art SiC Diode and MosFET Technologies During Ramp-Up Thomas Neyer, ON Semiconductor SiC Device Reliability Don Gajewski, Wolfspeed



WWW.POWERAMERICAINSTITUTE.ORG

## Stop by and see us at booth #466!

Visit our member booths:









#711

#1065 #1364 #1224

DIAMOND SPONSOR



#1241



#611



#332



#529

